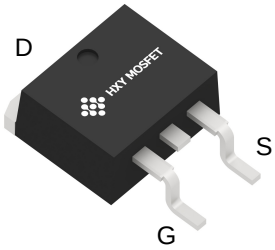
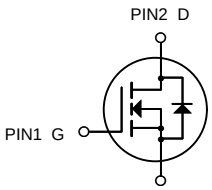
Description

The IRFZ44NS uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO-263
(D2PAK)



N-Channel MOSFET

General Features

V_{DS} = 55V I_D =49A

$R_{DS(ON)}$ < 13mΩ @ V_{GS}=10V

Application

Switching application

Power Management for Inverter Systems.

Ordering Information

Product ID	Pack	Brand	Units/Tube)
IRFZ44NS	TO-263(D2PAK)	HXY MOSFET	50

Absolute Maximum Ratings (T_C =25°C unless otherwise noted)

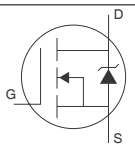
Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	55	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	49	A
I_D (100°C)	Drain Current-Continuous(T_C=100°C)	35	A
I_{DM}	Pulsed Drain Current	160	A
P_D	Maximum Power Dissipation	94	W
E_{AR}	Repetitive Avalanche Energy	9.4	mJ
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	℃
$R_{\theta JC}$	Thermal Resistance,Junction-to-Case(Note 2)	1.5	℃/W

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	——	——	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.058	——	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	10	13	mΩ	V_{GS} = 10V, I_D = 25A④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	——	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
g_{fs}	Forward Transconductance	19	——	——	S	V_{DS} = 25V, I_D = 25A④
I_{DSS}	Drain-to-Source Leakage Current	——	——	25	μA	V_{DS} = 55V, V_{GS} = 0V
		——	——	250		V_{DS} = 44V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -20V
Q_g	Total Gate Charge	——	——	63	nC	I_D = 25A
Q_{gs}	Gate-to-Source Charge	——	——	14		V_{DS} = 44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	——	23		V_{GS} = 10V, See Fig. 6 and 13
$t_{d(on)}$	Turn-On Delay Time	——	12	——	ns	V_{DD} = 28V
t_r	Rise Time	——	60	——		I_D = 25A
$t_{d(off)}$	Turn-Off Delay Time	——	44	——		R_G = 12Ω
t_f	Fall Time	——	45	——		V_{GS} = 10V, See Fig. 10 ④
L_S	Internal Source Inductance	——	7.5	——	nH	Between lead, and center of die contact
C_{iss}	Input Capacitance	——	1470	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	360	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	88	——		f = 1.0MHz, See Fig. 5
E_{AS}	Single Pulse Avalanche Energy②	——	530⑤	150⑥	mJ	I_{AS} = 25A, L = 0.47mH

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	49	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode)①	——	——	160		
V_{SD}	Diode Forward Voltage	——	——	1.3	V	T_J = 25°C, I_S = 25A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	——	63	95	ns	T_J = 25°C, I_F = 25A
Q_{rr}	Reverse Recovery Charge	——	170	260	nC	di/dt = 100A/μs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				



Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 0.48mH R_G = 25Ω, I_{AS} = 25A. (See Figure 12)

③ I_{SD} ≤ 25A, di/dt ≤ 230A/μs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 175°C

④ Pulse width ≤ 400μs; duty cycle ≤ 2%.

⑤ This is a typical value at device destruction and represents operation outside rated limits.

⑥ This is a calculated value limited to T_J = 175°C .

** When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

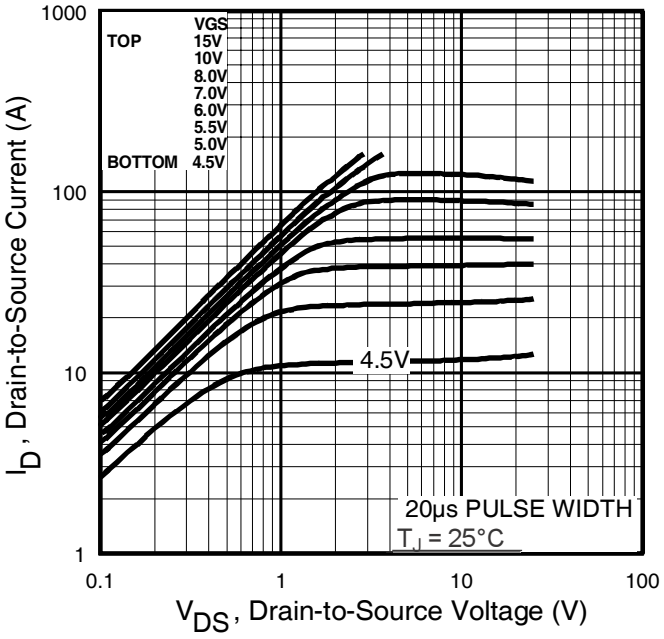


Fig 1. Typical Output Characteristics

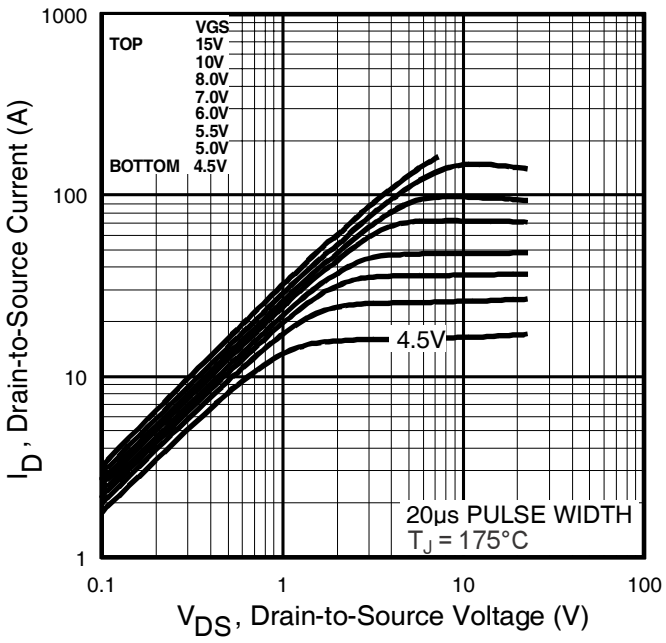


Fig 2. Typical Output Characteristics

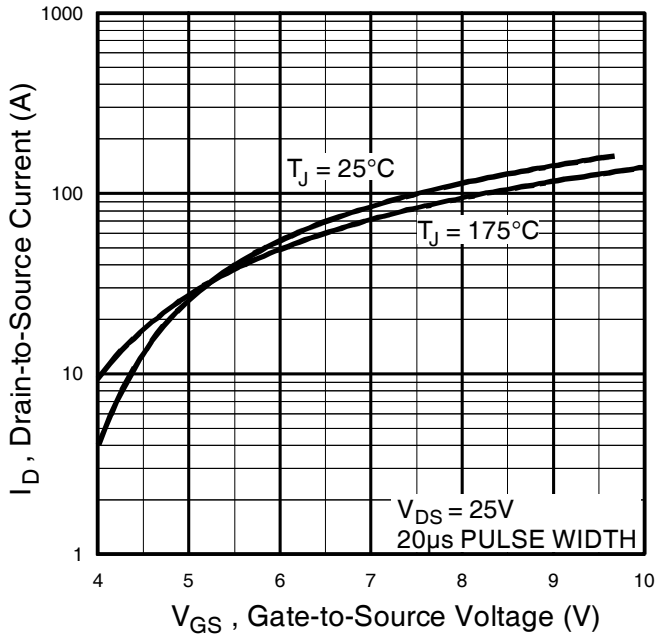


Fig 3. Typical Transfer Characteristics

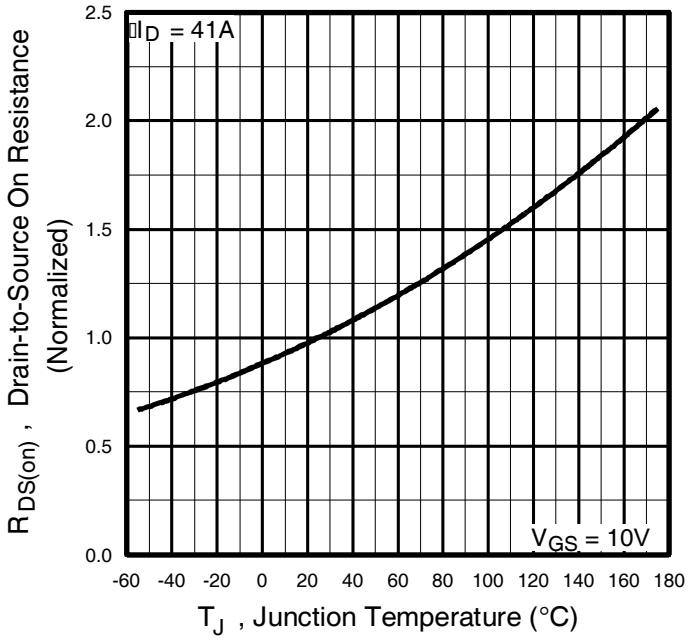


Fig 4. Normalized On-Resistance Vs. Temperature

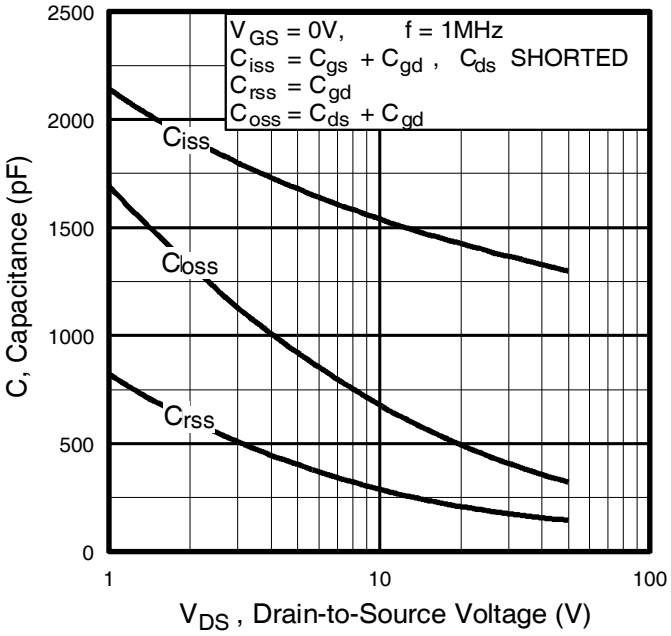


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

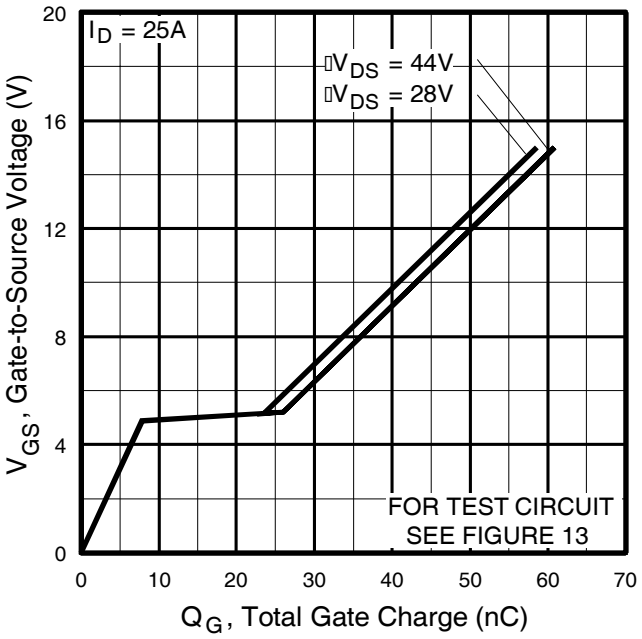


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

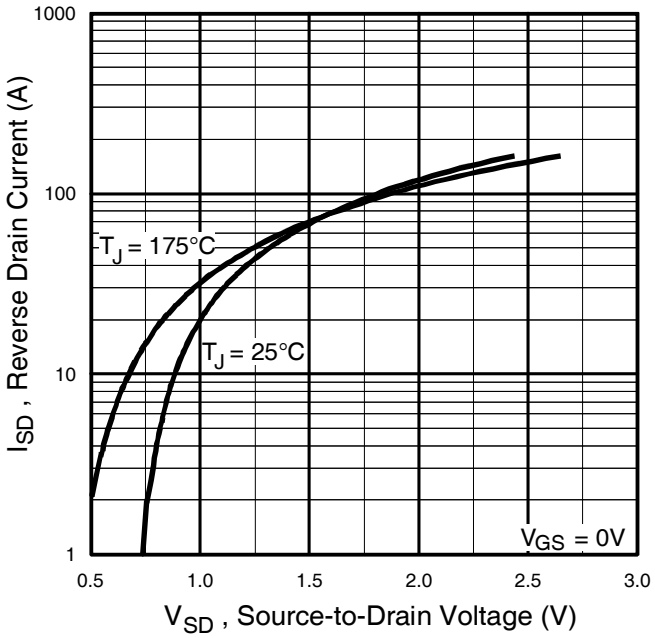


Fig 7. Typical Source-Drain Diode Forward Voltage

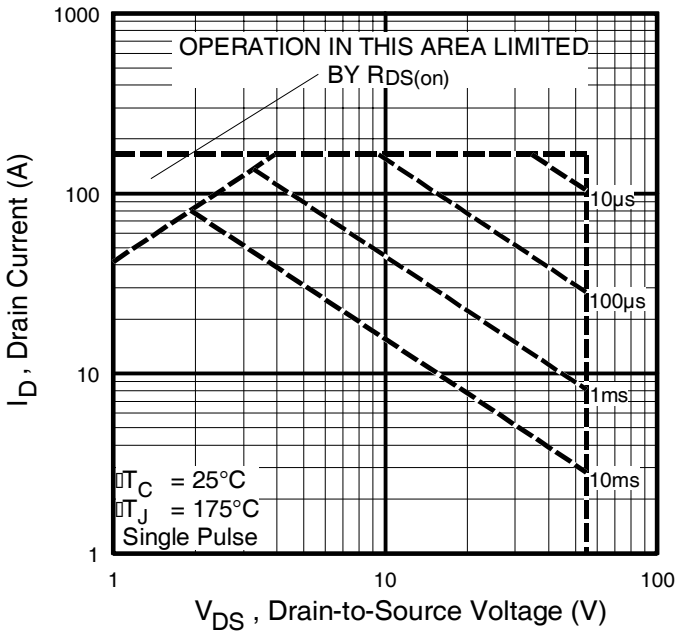


Fig 8. Maximum Safe Operating Area

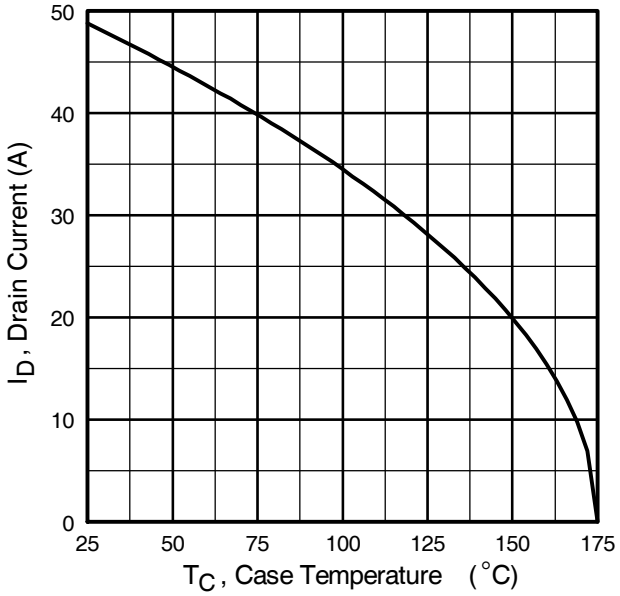


Fig 9. Maximum Drain Current Vs. Case Temperature

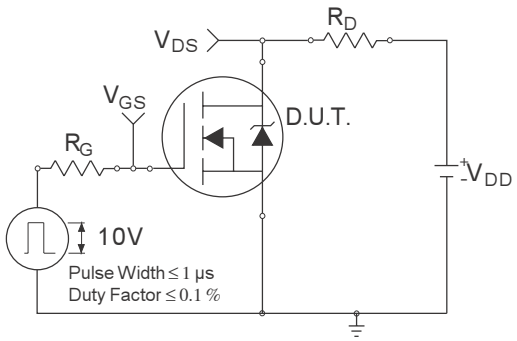


Fig 10a. Switching Time Test Circuit

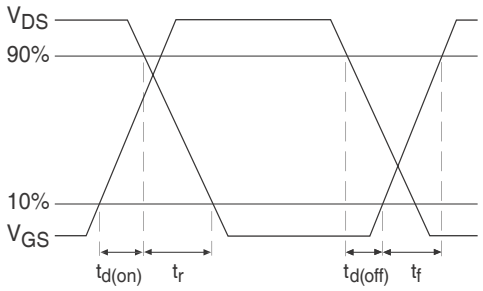


Fig 10b. Switching Time Waveforms

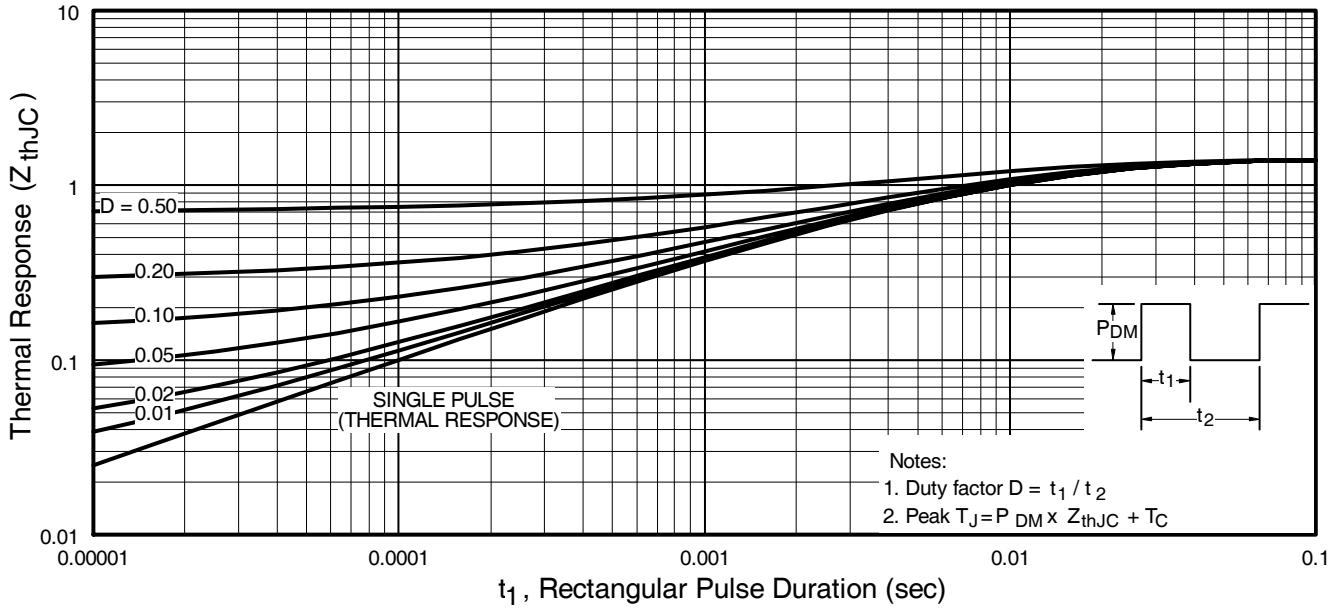


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

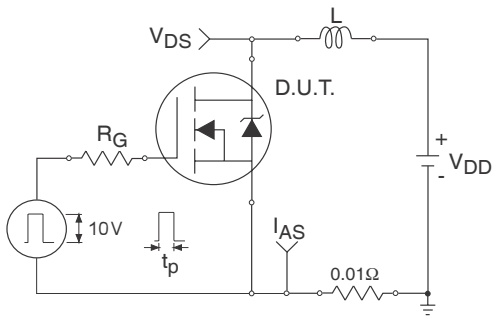


Fig 12a. Unclamped Inductive Test Circuit

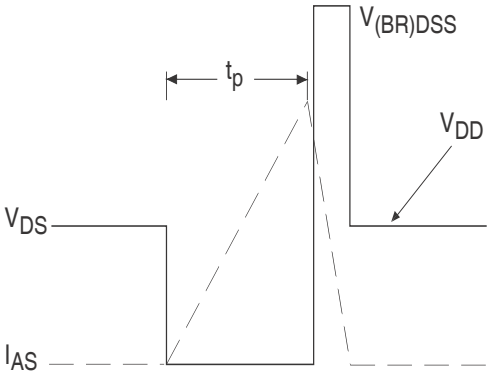


Fig 12b. Unclamped Inductive Waveforms

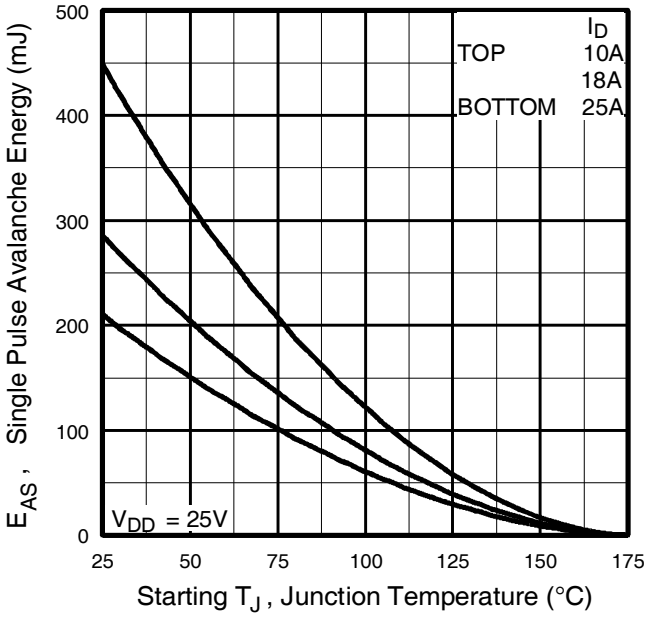


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

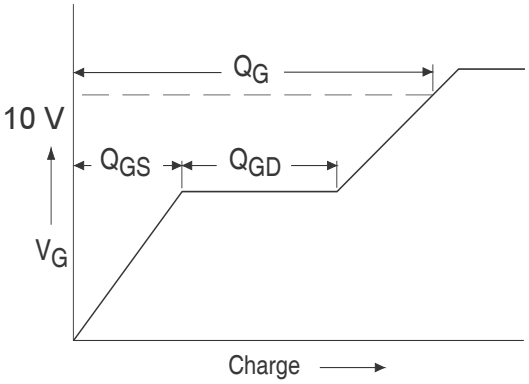


Fig 13a. Basic Gate Charge Waveform

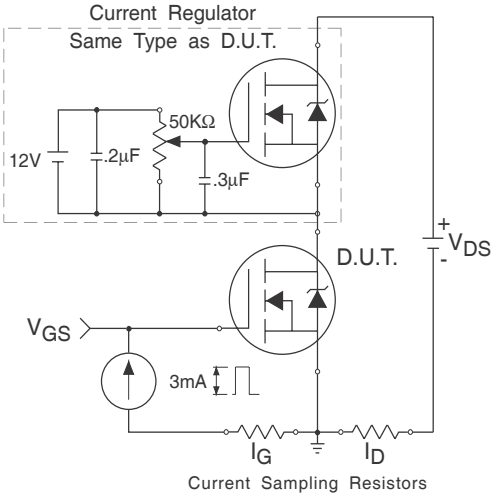
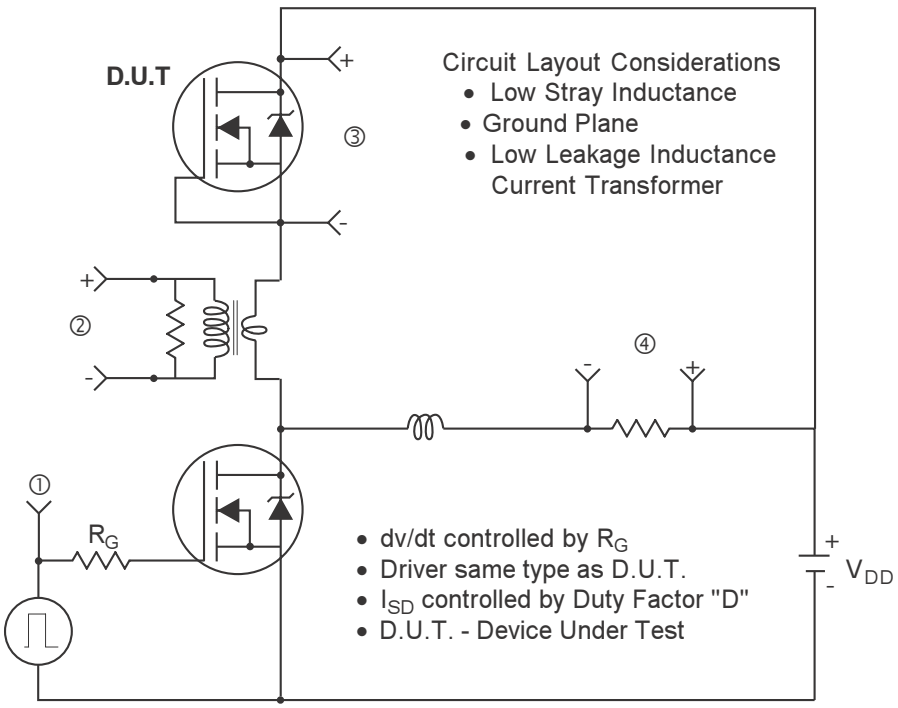


Fig 13b. Gate Charge Test Circuit



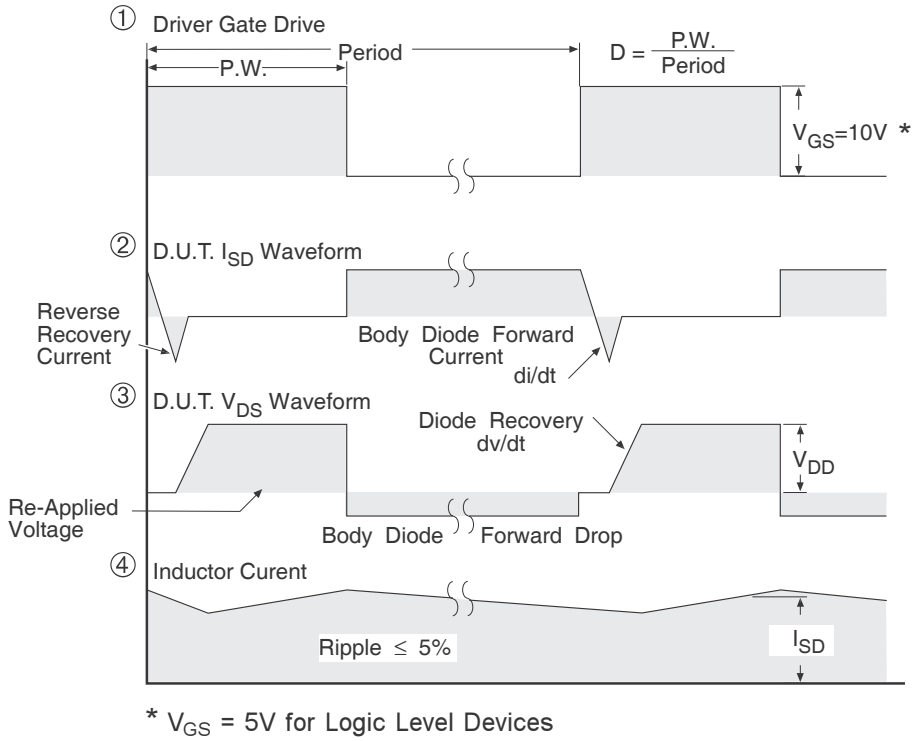
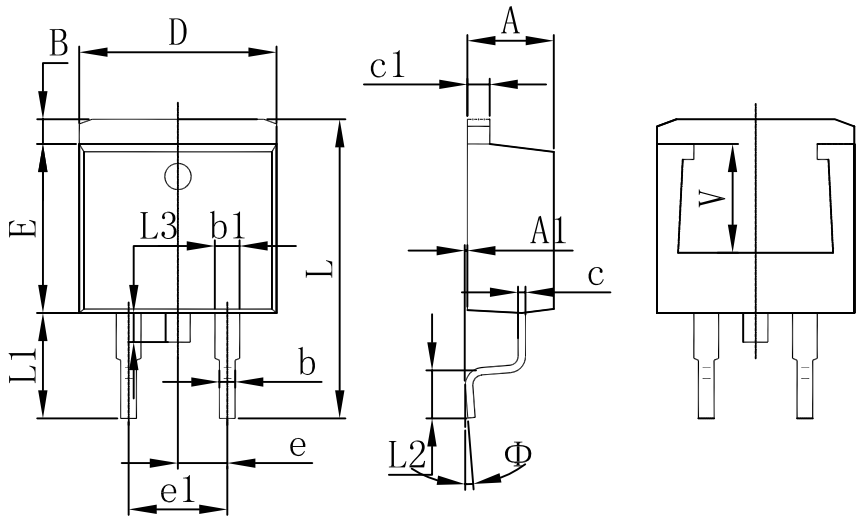


Fig 14. For N-Channel HEXFETS

TO-263(D2PAK) Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.120	1.420	0.044	0.056
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	14.940	15.500	0.588	0.610
L1	4.950	5.450	0.195	0.215
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
Φ	0°	8°	0°	8°
V	5.600 REF.		0.220REF.	

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